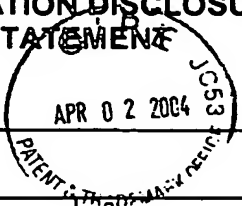


INFORMATION DISCLOSURE STATEMENT		Atty Docket: Serial No.: Applicant: Filing Date: Group:		59921 10/803,467 CHAI ET AL. MARCH 18, 2004			
<div style="text-align: center;">  U.S. PATENT DOCUMENTS </div>							
Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
<i>DB</i>	AA	5,625,202	4/29/97	Chai	257	94	
<i>DB</i>	AB	5,834,331	11/10/98	Razeghi	438	40	
<i>DB</i>	AC	5,917,196	6/29/99	Teraguchi	257	22	
<i>DB</i>	AD	6,043,514	3/28/00	Teraguchi	257	94	
<i>DB</i>	AE	6,078,064	6/20/00	Ming-Jiunn et al.	257	103	
<i>DB</i>	AF	6,218,280	4/17/01	Kryliouk et al.	438	607	
<i>DB</i>	AG	6,271,104	8/7/01	Razeghi et al.	438	481	
<i>DB</i>	AH	6,280,523	8/28/01	Coman et al.	117	101	
<i>DB</i>	AI	6,303,405	10/16/01	Yoshida et al.	438	46	
<i>DB</i>	AJ	6,350,666	2/26/02	Kryliouk	438	604	
<i>DB</i>	AK	6,380,108	4/30/02	Linthicum et al.	438	791	
<i>DB</i>	AL	6,420,199	7/16/02	Coman et al.	438	22	
<i>DB</i>	AM	6,498,113	2/24/02	Solomon et al.	438	778	
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation
<i>DB</i>	AM	JP10215028	08/11/98	Japan	H01S3	18	English Abstract
	AN						
	AO						
OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)							
<i>DB</i>	AQ	"Growth of M-Plane Gan (1100): A Way to Evade Electrical Polarization in Nitrides" Physica Status Solida (A) Applied Research, Vol. 180, No. 1, Pgs R1 to R4, 1 to 408, July 16, 2000, Wiley-VCH, ISSN 0031-8965 phys.stat.sol (a), Berlin 180 (2000)1, www.interscience.wiley.com					
<i>DB</i>	AR	"Epitaxial Growth and Orientation of GaN on (1 0 0) g-LiAlO ₂ ", Volume 2, Article 30, MRS Internet Journal of Nitride Semiconductor Research, 1997 The Materials Research Society					
<i>DB</i>	AS	"Nitride Semiconductors Free of Electrostatic Fields for Efficient White Light-Emitting Diodes", Nature, Vol. 406, 24 August 2000, www.nature.com , 2000 Macmillan Magazines Ltd.					
EXAMINER: <i>[Signature]</i>				DATE CONSIDERED: <i>8/31/05</i>			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

**INFORMATION DISCLOSURE
STATEMENT**

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Atty Docket:
Serial No.:
Applicant:
Filing Date:
Group:59921
10/803,467
CHAI ET AL.
MARCH 18, 2004**U.S. PATENT DOCUMENTS**

Examiner Initials		Document Number	Date	Name	Class	Sub Class	Filing Date
<i>AS</i>	AT	20030024475	2/6/03	Anderson	118	715	
<i>AS</i>	AV	6,518,079	2/11/03	Imler	438	33	
<i>AS</i>	AW	6,521,914	2/18/03	Krames et al.	257	81	
<i>AS</i>	AX	6,534,795	3/18/03	Hori et al.	257	79	
<i>AS</i>	AY	20030102482	6/5/03	Saxler	257	85	
<i>AS</i>	AZ	20030180580	9/25/03	Wada et al.	428	698	
<i>AS</i>	BA	20030182158	10/2/03	Maruska et al.	117	84	
<i>AS</i>	BB	6,630,689	10/7/03	Bhat et al.	257	79	
<i>AS</i>	BC	20030198837	10/23/03	Craven et al.	428	698	
<i>AS</i>	BD	6,648,966	11/18/03	Maruska et al.	117	101	
	BE						
	BF						
	BG						

FOREIGN PATENT DOCUMENTS

		Document Number	Date	Country	Class	Sub Class	Translation
	BH						
	BI						
	BJ						
	BK						

OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)

	BL	
	BM	
	BN	

EXAMINER:

R. M. H.

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8/31/05

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